

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It is suitable for automotive application.

Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- BLDC Motor driver
- DC-DC
- Battery protection

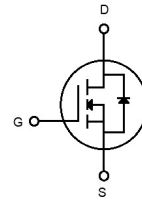
Ordering Information:

Part NO.	ZMSA010N04HB6
Marking	ZMS010N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	800

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	155	A
	I_D	$T_C=75^\circ\text{C}$	155	A
	I_D	$T_C=100^\circ\text{C}$	153	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	465	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	188	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	5.0	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	320	mJ
		$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	460	mJ
ESD Level (HBM)	CLASS 2			

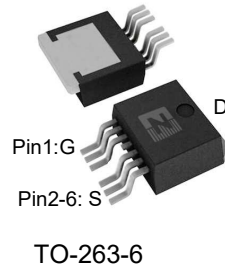
Product Summary



$$V_{DS} = 40\text{V}$$

$$R_{DS(ON)} = 0.9\text{m}\Omega$$

$$I_D = 155\text{A}$$



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.8	°C/W
Thermal resistance, junction-ambient ^②	R_{thJA}		-	30	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$		0.9	1.3	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=20A$		30		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	6900	-	pF
Output capacitance	C_{oss}		-	2100	-	
Reverse transfer capacitance	C_{rss}		-	86	-	
Gate Resistance	R_g	$f=1MHz$	-	1.4	-	Ω
Total gate charge	Q_g	$V_{DD}=15V,$ $I_D=40A,$ $V_{GS}=10V$	-	94	-	nC
Gate - Source charge	Q_{gs}		-	21	-	
Gate - Drain charge	Q_{gd}		-	26	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V,$ $R_G=3.3\Omega, I_D=20A$	-	39	-	ns
Turn-ON Rise time	t_r		-	42	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	31	-	ns
Turn-Off Fall time	t_f		-	12	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, di_S/dt=$ $100A/\mu s, I_S=50A$	-	72	-	ns
Reverse Recovery Charge	Q_{RR}		-	85	-	nC



Fig.1 Gate-Charge Characteristics

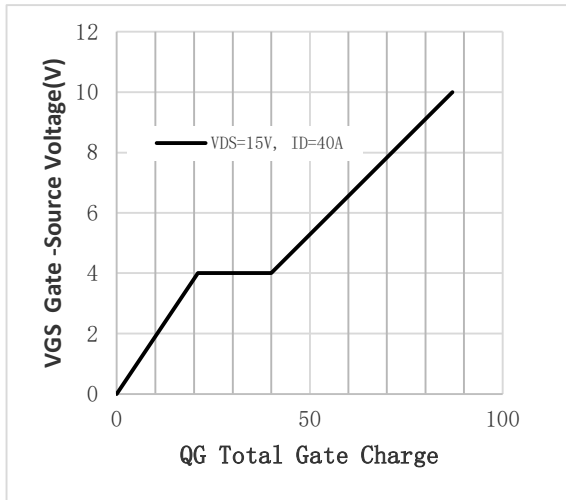


Fig.2 Capacitance Characteristics

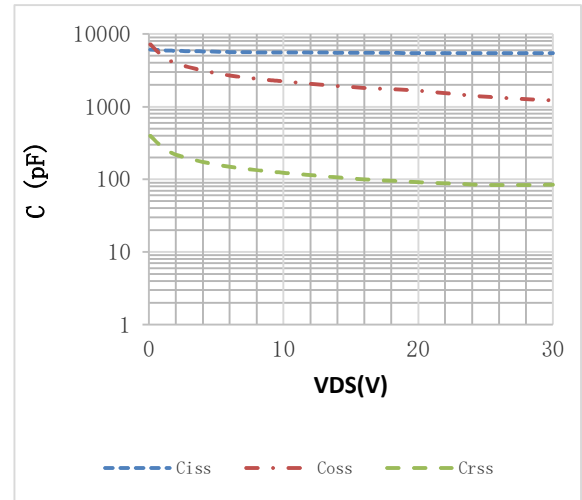


Fig.3 Power Dissipation

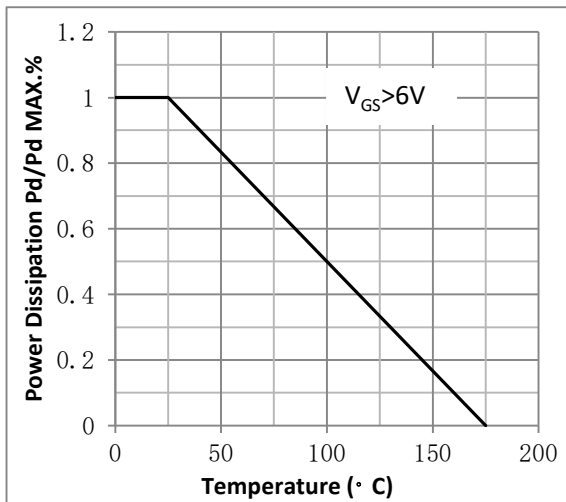


Fig.4 Typical output Characteristics

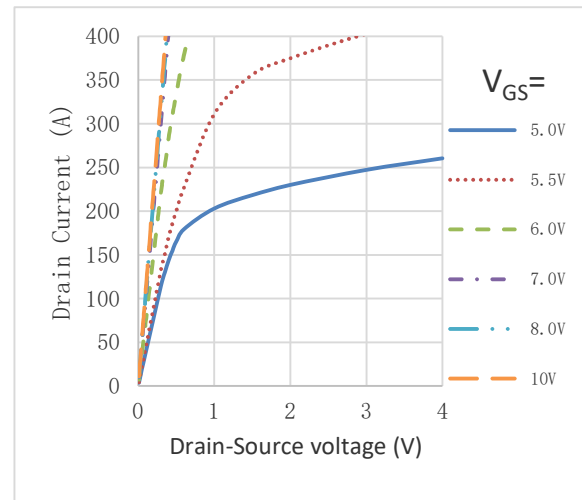


Fig.5 Threshold Voltage V.S Junction Temperature

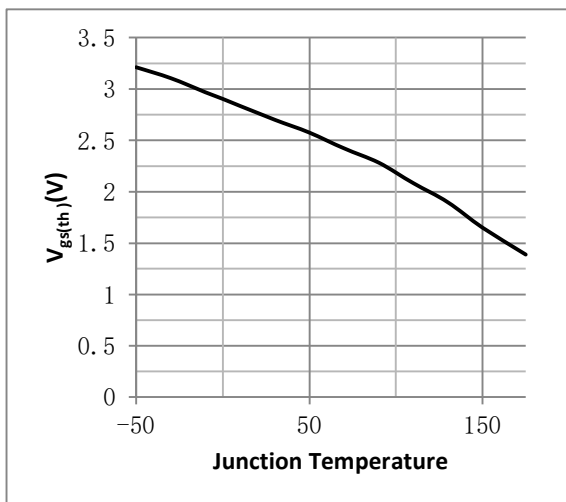


Fig.6 Resistance V.S Drain Current

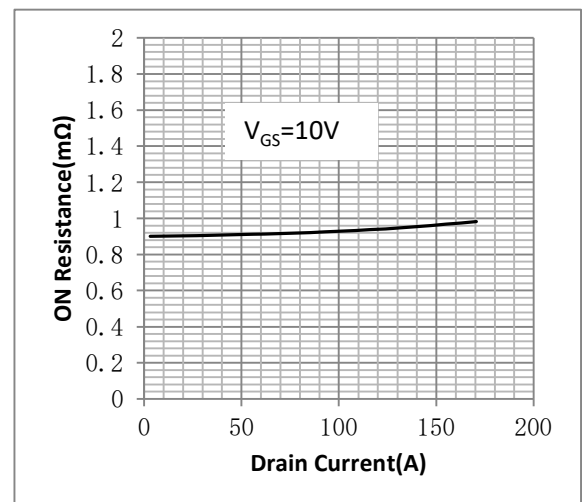


Fig.7 On-Resistance VS Gate Source Voltage

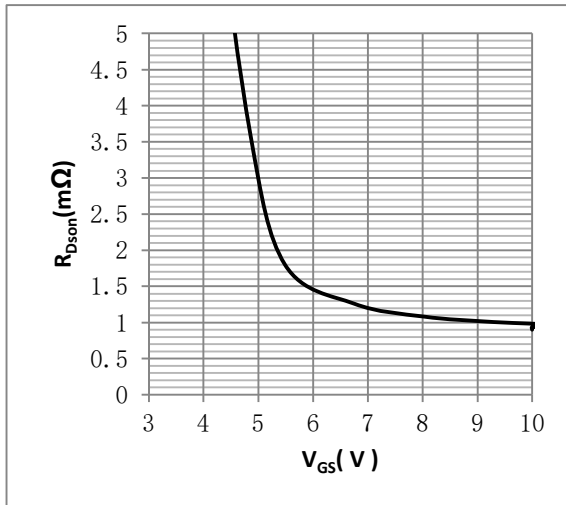


Fig.8 On-Resistance V.S Junction Temperature

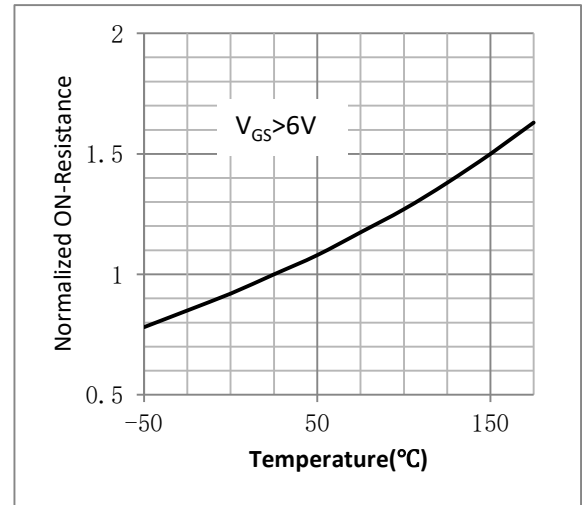


Figure 9. Diode Forward Voltage vs. Current

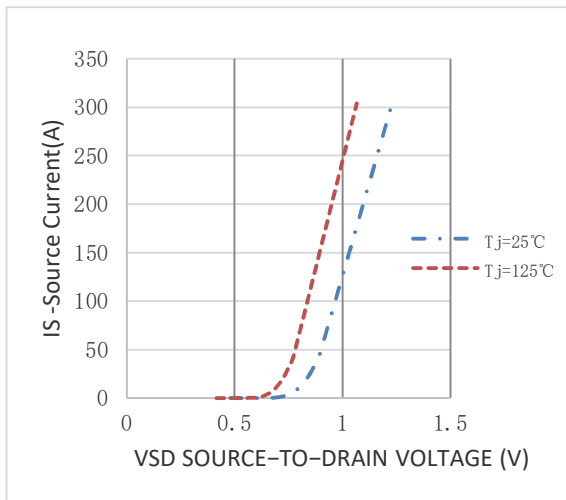


Figure 10. Transfer Characteristics

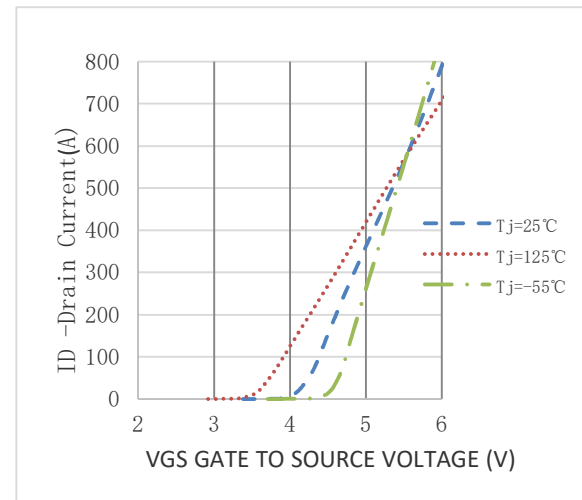


Fig.11 Safe Operating Area

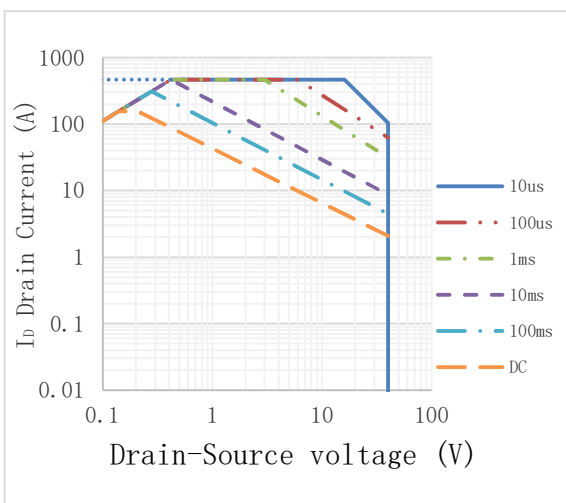
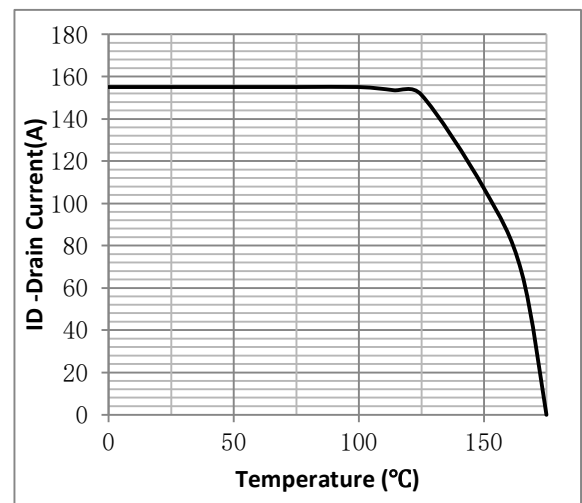
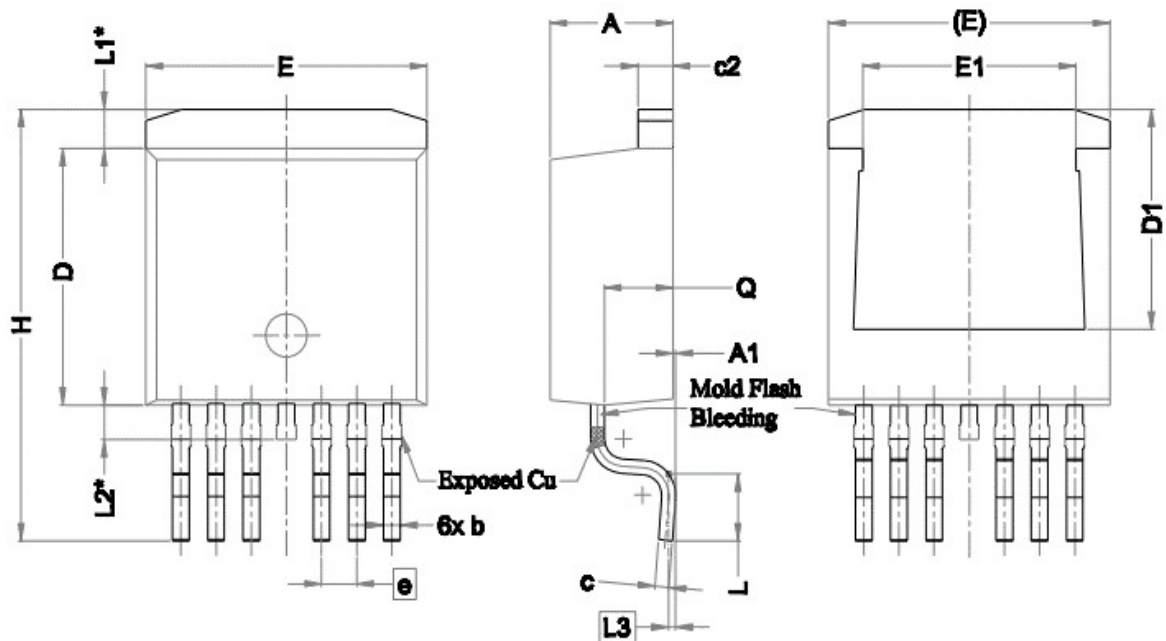


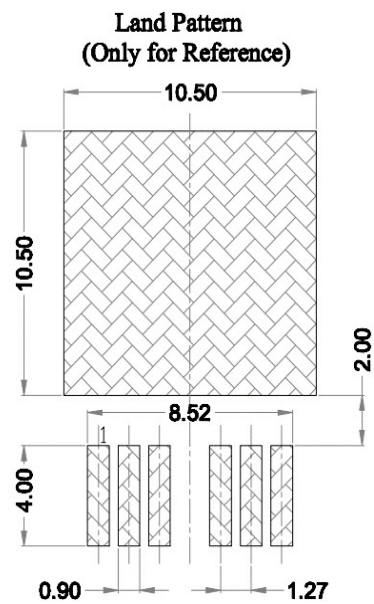
Fig.12 I_D vs. Case Temperature^③



•TO-263-6 Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours ;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.6.6	
B	2022.9.5	1.Add Reach,HF figure,2.ID modify
C	2022.11.14	1.Add Dynamic characteristics max limit 2.Add details of dimension drawing
D	2022.12.20	1.Modified id curve , junction temperature change to case
E	2024.1.16	Modified ciss,Qg,switch time
F	2024.8.20	Correct POD